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PATENT & TRADEMARK OFFICE

	Atty Docket No.	Serial No.
	M-799-4C US	08/851,608
SUMMARY OF CITED DOCUMENTS		Applicants: Bulucea et al.
	Filing Date	Group
	5 May 1997	2811

U.S. Patent Documents

Document Number	Date	Name	Class	Subclass
3,412,297	11/19/68	Amlinger	317	235
3,924,265	12/2/75	Rodgers	357	23
4,145,700	03/20/79	Jambotkar	357	23
4,148,047	04/03/79	Hendrickson	357	23
4,345,265	08/17/82	Blanchard	357	23
4,364,074	12/14/82	Garnache et al.	357	23
4,374,455	02/22/83	Goodman	29	571
4,376,286	03/08/83	Lidow et al.	357	23
4,398,339	08/16/83	Blanchard et al.	29	571
4,420,379	12/13/83	Tonnel	204	38
4,443,931	04/24/84	Baliga et al.	29	571
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4,532,534	07/30/85	Ford et al.	357	23.4
4,593,302	06/03/86	Lidow et al.	357	23.4
4,631,564	12/23/86	Neilson et al.	357	23.4
4,663,644	05/05/87	Shimizu	357	23.14
4,680,853	07/21/87	Lidow et al.	29	571
4,764,481	08/16/88	Alvi et al.	437	56
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4,783,694	11/08/88	Merrill et al.	357	51
4,794,561	12/27/88	Hsu	365	182
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4,824,793	04/25/89	Richardson et al.	437	47
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	55-146976	11/15/80	Japan	
	57-18365	01/30/82	Japan	
	57-72365	05/06/82	Japan	
	58-137254	08/15/83	Japan	
	59-80970	05/10/84	Japan	
	59-181668	10/16/84	Japan	
	59-193064	11/01/84	Japan	
	60-28271	02/13/85	Japan	
	62-12167	01/21/87	Japan	
	62-16572	01/24/87	Japan	
	62-37965	02/18/87	Japan	
	63-114173	05/19/88	Japan	
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U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-799-4C US	08/851,608
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicants: Bulucea et al.	
(Use several sheets if necessary)		Filing Date	Group
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
SWL	AA	3,412,297	Nov. 19, 1968	Amlinger	317	235	
	AB	3,924,265	Dec. 2, 1975	Rodgers	357	23	
	AC	4,364,074	Dec. 14, 1982	Garnache et al.	357	23	
	AD	4,374,455	Feb. 22, 1983	Goodman	29	571	
	AE	4,443,931	Apr. 24, 1984	Baliga et al.	29	571	
	AF	4,532,534	Jul. 30, 1985	Ford et al.	357	23.4	
SWL	AG	4,783,694	Nov. 08, 1988	Merrill et al.	357	51	

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	AK	57-72365	05/06/82	Japan			X
	AL	58-137254	08/15/83	Japan			X
	AM	59-80970	05/10/84	Japan			X
	AN	59-181668	10/16/84	Japan			X
	AO	59-193064	11/01/84	Japan			X
	AP	60-28271	02/13/85	Japan			X
	AQ	62-12167	01/21/87	Japan			X
	AR	62-16572	01/24/87	Japan			X
	AS	62-37965	02/18/87	Japan			X
	AT	63-114173	05/19/88	Japan			X
	AU	63-124762	08/15/88	Japan			X
SWL	AV	63-224260	09/19/88	Japan			X

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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)	BB	Kato et al., "A Study for High Voltage V-MOS Structure", <u>IEICE Trans. C</u> , Vol. 81, No. 7, ED 81 - 4, 1981, pgs. 25 - 32.	
)	BC	Katoh et al., "Design of New Structural High Breakdown Voltage V-MOSFET--Static Shield V-MOSFET", <u>Elec. and Comms. in Japan</u> , Vol. 66-C, No. 6, 1983, pgs. 95 - 105 for English version, pgs. 462 - 469 for Japanese version.	
)	BD	Katoh et al., "Design of High Breakdown Voltage V-MOSFET Applying Static Shield Effect", <u>Review Elec. Coms. Labs.</u> , Vol. 32, No. 6, 1984, pgs. 1107 - 1114 for English version, Vol. 33, No. 2, 1984, pgs. 257 - 268 for Japanese version.	
)	BE	Muller et al., <u>Device Electronics for Integrated Circuits</u> (John Wiley & Sons), 1977, pgs. 128-137.	
)	BF	Pelly et al., "Applying International Rectifier's HEXFET® Power MOSFETs", <u>HEXFET Databook, Power MOSFET Application and Product Data</u> (3d ed., International Rectifier), Appln. Note 930A, 1985, printed September 1984, pgs. A-11 to A-20.	
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)	BI	Sun et al., "Modeling of the On-Resistance of LDMOS, VDMOS, and VMOS Power Transistors," <u>IEEE Trans. Electron Devices</u> , February 1980, pgs. 356 - 367.	
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)	BL		
)	BM		
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